

## IN THE UNITED STATES PATENT AND TRADE MARKS OFFICE

Applicant:

Richard C. Foss et al

Serial No:

08/147,038

Filed:

November 4, 1993

Title:

METHOD FOR DRAM SENSING CURRENT CONTROL

Art Unit:

2502

Examiner:

T. Dinh

RECEIVED

2-19-94

Our File:

628.30050CX1

JUL 19 1994

**GROUP 2500** 

The Commissioner of Patents and Trade Marks, Washington, D.C., 20231 U.S.A.

July 6, 1994

Dear Sir:

This is in response to the official action dated January 6th, 1994 in the above-identified application.

Please amend the title on all papers which carry it to --DYNAMIC RANDOM ACCESS MEMORY USING IMPERFECT ISOLATING TRANSISTORS--.

## REMARKS

The title suggested by the Patent Office has been adopted. Withdrawal of the objection to the title is respectfully requested.

Claims 1-17 were rejected as anticipated by Wang. Applicant respectfully traverses the rejection for the following reasons.

Applicant's claim 1 defines high resistance controllable current leakage imporfect isolating means for